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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

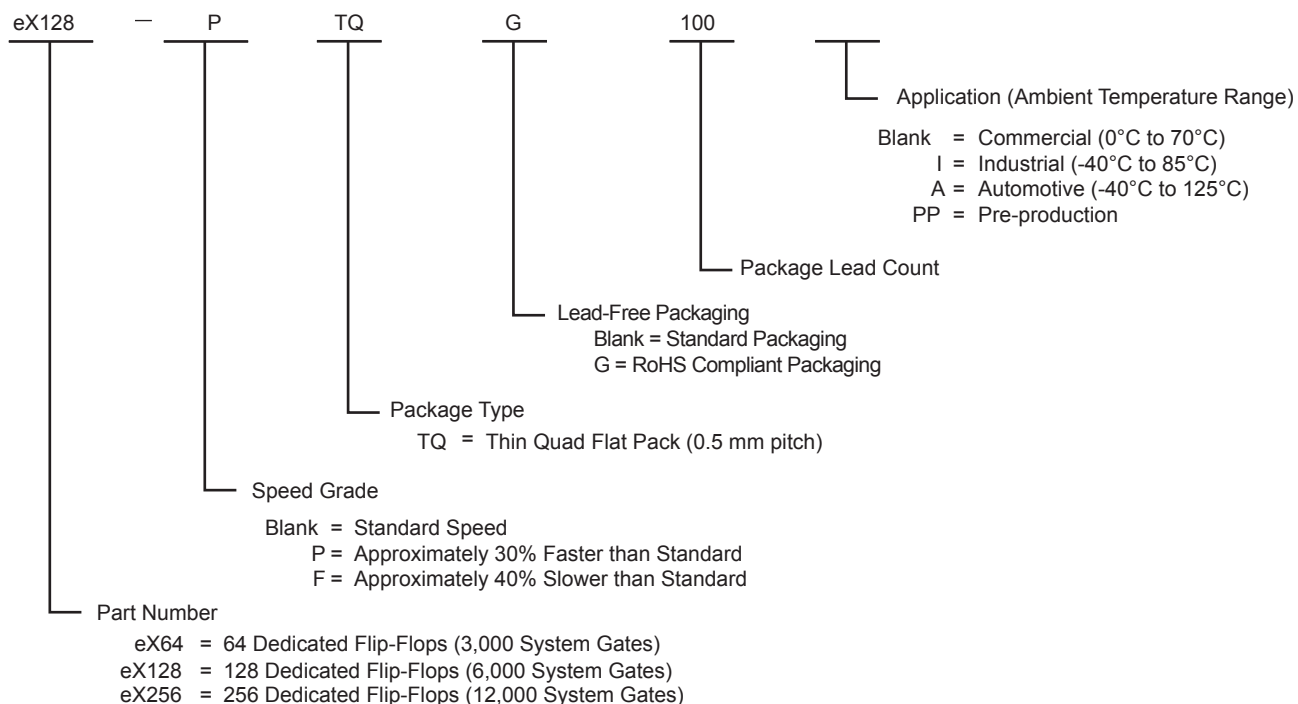
Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	128
Total RAM Bits	-
Number of I/O	41
Number of Gates	3000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	64-LQFP
Supplier Device Package	64-TQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/ex64-tq64

Ordering Information



eX Device Status

eX Devices	Status
eX64	Production
eX128	Production
eX256	Production

Plastic Device Resources

Device	User I/Os (Including Clock Buffers)	
	TQ64	TQ100
eX64	41	56
eX128	46	70
eX256	—	81

Note: TQ = Thin Quad Flat Pack

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1 – eX FPGA Architecture and Characteristics

General Description

The eX family of FPGAs is a low-cost solution for low-power, high-performance designs. The inherent low power attributes of the antifuse technology, coupled with an additional low static power mode, make these devices ideal for power-sensitive applications. Fabricated with an advanced 0.22 μm CMOS antifuse technology, these devices achieve high performance with no power penalty.

eX Family Architecture

Microsemi eX family is implemented on a high-voltage twin-well CMOS process using 0.22 μm design rules. The eX family architecture uses a “sea-of-modules” structure where the entire floor of the device is covered with a grid of logic modules with virtually no chip area lost to interconnect elements or routing. Interconnection among these logic modules is achieved using Microsemi patented metal-to-metal programmable antifuse interconnect elements. The antifuse interconnect is made up of a combination of amorphous silicon and dielectric material with barrier metals and has an “on” state resistance of 25Ω with a capacitance of 1.0fF for low-signal impedance. The antifuses are normally open circuit and, when programmed, form a permanent low-impedance connection. The eX family provides two types of logic modules, the register cell (R-cell) and the combinatorial cell (C-cell).

The R-cell contains a flip-flop featuring asynchronous clear, asynchronous preset, and clock enable (using the S0 and S1 lines) control signals ([Figure 1-1](#)). The R-cell registers feature programmable clock polarity selectable on a register-by-register basis. This provides additional flexibility while allowing mapping of synthesized functions into the eX FPGA. The clock source for the R-cell can be chosen from either the hard-wired clock or the routed clock.

The C-cell implements a range of combinatorial functions up to five inputs ([Figure 1-2 on page 1-2](#)). Inclusion of the DB input and its associated inverter function enables the implementation of more than 4,000 combinatorial functions in the eX architecture in a single module.

Two C-cells can be combined together to create a flip-flop to imitate an R-cell via the use of the CC macro. This is particularly useful when implementing non-timing-critical paths and when the design engineer is running out of R-cells. More information about the CC macro can be found in the [Maximizing Logic Utilization in eX, SX and SX-A FPGA Devices Using CC Macros](#) application note.

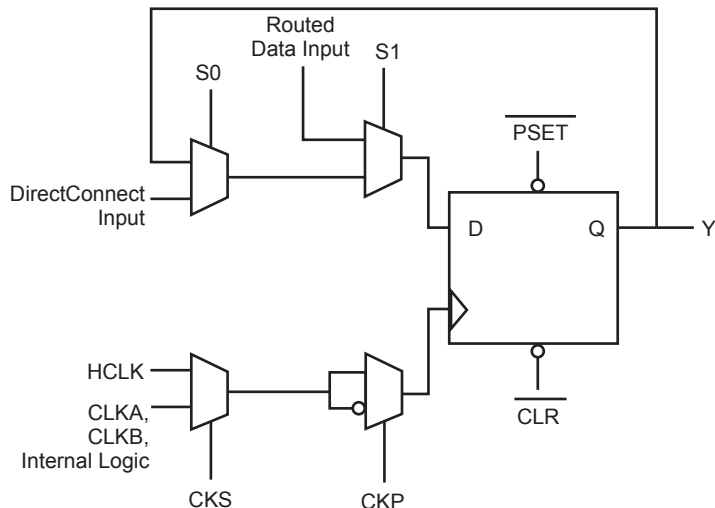


Figure 1-1 • R-Cell

Table 1-1 describes the possible connections of the routed clock networks, CLKA and CLKB. Unused clock pins must not be left floating and must be tied to HIGH or LOW.

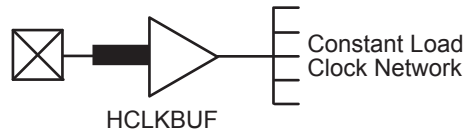


Figure 1-5 • eX HCLK Clock Pad

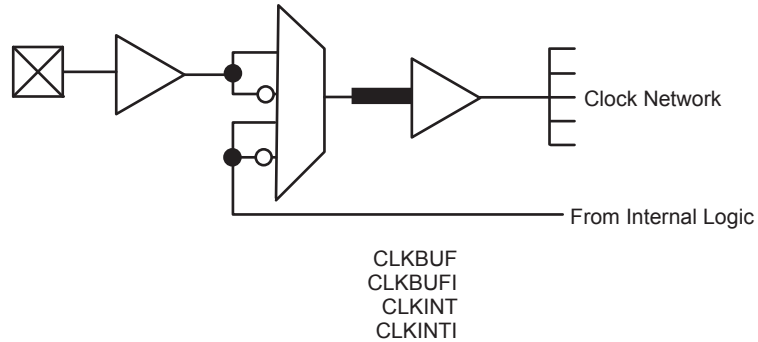


Figure 1-6 • eX Routed Clock Buffer

Table 1-1 • Connections of Routed Clock Networks, CLKA and CLKB

Module	Pins
C-Cell	A0, A1, B0 and B1
R-Cell	CLKA, CLKB, S0, S1, PSET, and CLR
I/O-Cell	EN

Table 1-2 describes the I/O features of eX devices. For more information on I/Os, refer to [Microsemi eX, SX-A, and RT54SX-S I/Os](#) application note.

Table 1-2 • I/O Features

Function	Description
Input Buffer Threshold Selection	<ul style="list-style-type: none"> • 5.0V TTL • 3.3V LVTTTL • 2.5V LVCMOS2
Nominal Output Drive	<ul style="list-style-type: none"> • 5.0V TTL/CMOS • 3.3V LVTTTL • 2.5V LVCMOS 2
Output Buffer	<p>“Hot-Swap” Capability</p> <ul style="list-style-type: none"> • I/O on an unpowered device does not sink current • Can be used for “cold sparing” <p>Selectable on an individual I/O basis</p> <p>Individually selectable low-slew option</p>
Power-Up	<p>Individually selectable pull ups and pull downs during power-up (default is to power up in tristate)</p> <p>Enables deterministic power-up of device</p> <p>V_{CCA} and V_{CCI} can be powered in any order</p>

The eX family supports mixed-voltage operation and is designed to tolerate 5.0 V inputs in each case.

A detailed description of the I/O pins in eX devices can be found in ["Pin Description"](#) on page 1-31.

Hot-Swapping

eX I/Os are configured to be hot-swappable. During power-up/down (or partial up/down), all I/Os are tristated, provided V_{CCA} ramps up within a diode drop of V_{CCI} . V_{CCA} and V_{CCI} do not have to be stable during power-up/down, and they do not require a specific power-up or power-down sequence in order to avoid damage to the eX devices. In addition, all outputs can be programmed to have a weak resistor pull-up or pull-down for output tristate at power-up. After the eX device is plugged into an electrically active system, the device will not degrade the reliability of or cause damage to the host system. The device's output pins are driven to a high impedance state until normal chip operating conditions are reached. Please see the application note, [Microsemi SX-A and RT54SX-S Devices in Hot-Swap and Cold-Sparing Applications](#), which also applies to the eX devices, for more information on hot swapping.

Power Requirements

Power consumption is extremely low for the eX family due to the low capacitance of the antifuse interconnects. The antifuse architecture does not require active circuitry to hold a charge (as do SRAM or EPROM), making it the lowest-power FPGA architecture available today.

Low Power Mode

The eX family has been designed with a Low Power Mode. This feature, activated with setting the special LP pin to HIGH for a period longer than 800 ns, is particularly useful for battery-operated systems where battery life is a primary concern. In this mode, the core of the device is turned off and the device consumes minimal power with low standby current. In addition, all input buffers are turned off, and all outputs and bidirectional buffers are tristated when the device enters this mode. Since the core of the device is turned off, the states of the registers are lost. The device must be re-initialized when returning to normal operating mode. I/Os can be driven during LP mode. For details, refer to the [Design for Low Power in Microsemi Antifuse FPGAs](#) application note under the section Using the LP Mode Pin on eX Devices. Clock pins should be driven either HIGH or LOW and should not float; otherwise, they will draw current and burn power. The device must be re-initialized when exiting LP mode.

Boundary Scan Testing (BST)

All eX devices are IEEE 1149.1 compliant. eX devices offer superior diagnostic and testing capabilities by providing Boundary Scan Testing (BST) and probing capabilities. These functions are controlled through the special test pins (TMS, TDI, TCK, TDO and TRST). The functionality of each pin is defined by two available modes: Dedicated and Flexible, and is described in [Table 1-4](#). In the dedicated test mode, TCK, TDI, and TDO are dedicated pins and cannot be used as regular I/Os. In flexible mode (default mode), TMS should be set HIGH through a pull-up resistor of 10 k Ω . TMS can be pulled LOW to initiate the test sequence.

Table 1-4 • Boundary Scan Pin Functionality

Dedicated Test Mode	Flexible Mode
TCK, TDI, TDO are dedicated BST pins	TCK, TDI, TDO are flexible and may be used as I/Os
No need for pull-up resistor for TMS and TDI	Use a pull-up resistor of 10 k Ω on TMS

Dedicated Test Mode

In Dedicated mode, all JTAG pins are reserved for BST; designers cannot use them as regular I/Os. An internal pull-up resistor is automatically enabled on both TMS and TDI pins, and the TMS pin will function as defined in the IEEE 1149.1 (JTAG) specification.

To select Dedicated mode, users need to reserve the JTAG pins in Microsemi's Designer software by checking the **Reserve JTAG** box in the Device Selection Wizard ([Figure 1-12](#)). JTAG pins comply with LVTTTL/TTL I/O specification regardless of whether they are used as a user I/O or a JTAG I/O. Refer to the ["3.3 V LVTTTL Electrical Specifications"](#) section and ["5.0 V TTL Electrical Specifications"](#) section on [page 1-18](#) for detailed specifications.



Figure 1-12 • Device Selection Wizard

Flexible Mode

In Flexible Mode, TDI, TCK and TDO may be used as either user I/Os or as JTAG input pins. The internal resistors on the TMS and TDI pins are disabled in flexible JTAG mode, and an external 10 k Ω pull-resistor to V_{CC1} is required on the TMS pin.

To select the Flexible mode, users need to clear the check box for **Reserve JTAG** in the Device Selection Wizard in Microsemi's Designer software. The functionality of TDI, TCK, and TDO pins is controlled by the BST TAP controller. The TAP controller receives two control inputs, TMS and TCK. Upon power-up, the TAP controller enters the Test-Logic-Reset state. In this state, TDI, TCK, and TDO function as user I/Os. The TDI, TCK, and TDO pins are transformed from user I/Os into BST pins when the TMS pin is LOW at the first rising edge of TCK. The TDI, TCK, and TDO pins return to user I/Os when TMS is held HIGH for at least five TCK cycles.

Programming

Device programming is supported through Silicon Sculptor series of programmers. In particular, Silicon Sculptor II is a compact, robust, single-site and multi-site device programmer for the PC.

With standalone software, Silicon Sculptor II allows concurrent programming of multiple units from the same PC, ensuring the fastest programming times possible. Each fuse is subsequently verified by Silicon Sculptor II to insure correct programming. In addition, integrity tests ensure that no extra fuses are programmed. Silicon Sculptor II also provides extensive hardware self-testing capability.

The procedure for programming an eX device using Silicon Sculptor II is as follows:

1. Load the *.AFM file
2. Select the device to be programmed
3. Begin programming

When the design is ready to go to production, Microsemi offers device volume-programming services either through distribution partners or via in-house programming from the factory.

For more details on programming eX devices, please refer to the [Programming Antifuse Devices](#) application note and the [Silicon Sculptor II User's Guide](#).

Probing Capabilities

eX devices provide internal probing capability that is accessed with the JTAG pins. The Silicon Explorer II Diagnostic hardware is used to control the TDI, TCK, TMS and TDO pins to select the desired nets for debugging. The user simply assigns the selected internal nets in the Silicon Explorer II software to the PRA/PRB output pins for observation. Probing functionality is activated when the BST pins are in JTAG mode and the TRST pin is driven HIGH or left floating. If the TRST pin is held LOW, the TAP controller will remain in the Test-Logic-Reset state so no probing can be performed. The Silicon Explorer II automatically places the device into JTAG mode, but the user must drive the TRST pin HIGH or allow the internal pull-up resistor to pull TRST HIGH.

When you select the **Reserve Probe Pin** box, as shown in [Figure 1-12 on page 1-10](#), the layout tool reserves the PRA and PRB pins as dedicated outputs for probing. This reserve option is merely a guideline. If the Layout tool requires that the PRA and PRB pins be user I/Os to achieve successful layout, the tool will use these pins for user I/Os. If you assign user I/Os to the PRA and PRB pins and select the **Reserve Probe Pin** option, Designer Layout will override the "Reserve Probe Pin" option and place your user I/Os on those pins.

To allow for probing capabilities, the security fuse must not be programmed. Programming the security fuse will disable the probe circuitry. [Table 1-8 on page 1-13](#) summarizes the possible device configurations for probing once the device leaves the Test-Logic-Reset JTAG state.

Silicon Explorer II Probe

Silicon Explorer II is an integrated hardware and software solution that, in conjunction with Microsemi Designer software tools, allow users to examine any of the internal nets of the device while it is operating in a prototype or a production system. The user can probe into an eX device via the PRA and PRB pins without changing the placement and routing of the design and without using any additional resources. Silicon Explorer II's noninvasive method does not alter timing or loading effects, thus shortening the debug cycle.

Silicon Explorer II does not require re-layout or additional MUXes to bring signals out to an external pin, which is necessary when using programmable logic devices from other suppliers.

Silicon Explorer II samples data at 100 MHz (asynchronous) or 66 MHz (synchronous). Silicon Explorer II attaches to a PC's standard COM port, turning the PC into a fully functional 18-channel logic analyzer. Silicon Explorer II allows designers to complete the design verification process at their desks and reduces verification time from several hours per cycle to a few seconds.

The Silicon Explorer II tool uses the boundary scan ports (TDI, TCK, TMS and TDO) to select the desired nets for verification. The selected internal nets are assigned to the PRA/PRB pins for observation. [Figure 1-13 on page 1-13](#) illustrates the interconnection between Silicon Explorer II and the eX device to perform in-circuit verification.

Design Considerations

The TDI, TCK, TDO, PRA, and PRB pins should not be used as input or bidirectional ports. Since these pins are active during probing, critical signals input through these pins are not available while probing. In addition, the Security Fuse should not be programmed because doing so disables the probe circuitry. It is recommended to use a series 70Ω termination resistor on every probe connector (TDI, TCK, TMS, TDO, PRA, PRB). The 70Ω series termination is used to prevent data transmission corruption during probing and reading back the checksum.

Table 1-8 • Device Configuration Options for Probe Capability (TRST pin reserved)

JTAG Mode	TRST ¹	Security Fuse Programmed	PRA, PRB ²	TDI, TCK, TDO ²
Dedicated	LOW	No	User I/O ³	Probing Unavailable
Flexible	LOW	No	User I/O ³	User I/O ³
Dedicated	HIGH	No	Probe Circuit Outputs	Probe Circuit Inputs
Flexible	HIGH	No	Probe Circuit Outputs	Probe Circuit Inputs
–	–	Yes	Probe Circuit Secured	Probe Circuit Secured

Notes:

1. If TRST pin is not reserved, the device behaves according to TRST = HIGH in the table.
2. Avoid using the TDI, TCK, TDO, PRA, and PRB pins as input or bidirectional ports. Since these pins are active during probing, input signals will not pass through these pins and may cause contention.
3. If no user signal is assigned to these pins, they will behave as unused I/Os in this mode. Unused pins are automatically tristated by Microsemi Designer software.

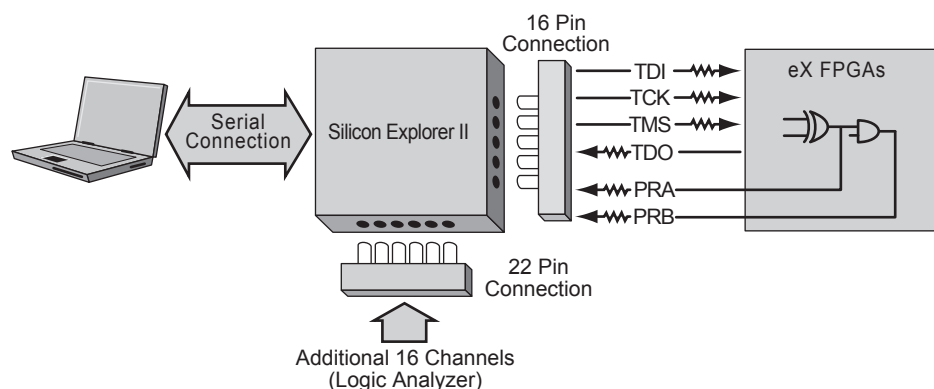


Figure 1-13 • Silicon Explorer II Probe Setup

Development Tool Support

The eX family of FPGAs is fully supported by both Libero® Integrated Design Environment and Designer FPGA Development software. Libero IDE is a design management environment that streamlines the design flow. Libero IDE provides an integrated design manager that seamlessly integrates design tools while guiding the user through the design flow, managing all design and log files, and passing necessary design data among tools. Additionally, Libero IDE allows users to integrate both schematic and HDL synthesis into a single flow and verify the entire design in a single environment. Libero IDE includes Synplify® for Microsemi from Synplicity®, ViewDraw for Microsemi from Mentor Graphics, ModelSim® HDL Simulator from Mentor Graphics®, WaveFormer Lite™ from SynaptiCAD™, and Designer software from Microsemi. Refer to the [Libero IDE flow](#) (located on Microsemi SoC Product Group's website) diagram for more information.

2.5 V / 3.3 V / 5.0 V Operating Conditions

Table 1-9 • Absolute Maximum Ratings*

Symbol	Parameter	Limits	Units
VCCI	DC Supply Voltage for I/Os	−0.3 to +6.0	V
VCCA	DC Supply Voltage for Array	−0.3 to +3.0	V
VI	Input Voltage	−0.5 to +5.75	V
VO	Output Voltage	−0.5 to +V _{CCI}	V
T _{STG}	Storage Temperature	−65 to +150	°C

Note: *Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Devices should not be operated outside the Recommended Operating Conditions.

Table 1-10 • Recommended Operating Conditions

Parameter	Commercial	Industrial	Units
Temperature Range*	0 to +70	−40 to +85	°C
2.5V Power Supply Range (VCCA, VCCI)	2.3 to 2.7	2.3 to 2.7	V
3.3V Power Supply Range (VCCI)	3.0 to 3.6	3.0 to 3.6	V
5.0V Power Supply Range (VCCI)	4.75 to 5.25	4.75 to 5.25	V

Note: *Ambient temperature (T_A).

Table 1-11 • Typical eX Standby Current at 25°C

Product	VCCA = 2.5 V VCCI = 2.5 V	VCCA = 2.5 V VCCI = 3.3 V	VCCA = 2.5 V VCCI = 5.0 V
eX64	397 μA	497 μA	700 μA
eX128	696 μA	795 μA	1,000 μA
eX256	698 μA	796 μA	2,000 μA

3.3 V LVTTTL Electrical Specifications

Symbol	Parameter		Commercial		Industrial		Units
			Min.	Max.	Min.	Max.	
VOH	VCCI = MIN, VI = VIH or VIL	(IOH = -8 mA)	2.4		2.4		V
VOL	VCCI = MIN, VI = VIH or VIL	(IOL = 12 mA)		0.4		0.4	V
VIL	Input Low Voltage			0.8		0.8	V
VIH	Input High Voltage		2.0	VCCI +0.5	2.0	VCCI +0.5	V
IIL/ IIH	Input Leakage Current, VIN = VCCI or GND		-10	10	-10	10	μA
IOZ	3-State Output Leakage Current, VOUT = VCCI or GND		-10	10	-10	10	μA
t _R , t _{F1,2}	Input Transition Time			10		10	ns
C _{IO}	I/O Capacitance			10		10	pF
ICC ^{3,4}	Standby Current			1.5		10	mA
IV Curve	Can be derived from the IBIS model at www.microsemi.com/soc/custsup/models/ibis.html .						

Notes:

1. t_R is the transition time from 0.8 V to 2.0 V.
2. t_F is the transition time from 2.0 V to 0.8 V.
3. ICC max Commercial -F = 5.0 mA
4. ICC = ICCI + ICCA
5. JTAG pins comply with LVTTTL/TTL I/O specification regardless of whether they are used as a user I/O or a JTAG I/O.

5.0 V TTL Electrical Specifications

Symbol	Parameter		Commercial		Industrial		Units
			Min.	Max.	Min.	Max.	
VOH	VCCI = MIN, VI = VIH or VIL	(IOH = -8 mA)	2.4		2.4		V
VOL	VCCI = MIN, VI = VIH or VIL	(IOL = 12 mA)		0.4		0.4	V
VIL	Input Low Voltage			0.8		0.8	V
VIH	Input High Voltage		2.0	VCCI +0.5	2.0	VCCI +0.5	V
IIL/ IIH	Input Leakage Current, VIN = VCCI or GND		-10	10	-10	10	μA
IOZ	3-State Output Leakage Current, VOUT = VCCI or GND		-10	10	-10	10	μA
t _R , t _{F1,2}	Input Transition Time			10		10	ns
C _{IO}	I/O Capacitance			10		10	pF
ICC ^{3,4}	Standby Current			15		20	mA
IV Curve	Can be derived from the IBIS model at www.microsemi.com/soc/custsup/models/ibis.html .						

Note:

1. t_R is the transition time from 0.8 V to 2.0 V.
2. t_F is the transition time from 2.0 V to 0.8 V.
3. ICC max Commercial -F=20mA
4. ICC = ICCI + ICCA
5. JTAG pins comply with LVTTTL/TTL I/O specification regardless of whether they are used as a user I/O or a JTAG I/O.

The estimation of the dynamic power dissipation is a piece-wise linear summation of the power dissipation of each component.

$$\begin{aligned} \text{Dynamic power dissipation} = & V_{CCA}^2 * [(m_c * C_{eqcm} * f_{mC})_{\text{Comb Modules}} + (m_s * C_{eqsm} * f_{mS})_{\text{Seq Modules}} \\ & + (n * C_{eqi} * f_n)_{\text{Input Buffers}} + (0.5 * (q1 * C_{eqcr} * f_{q1}) + (r1 * f_{q1}))_{\text{RCLKA}} + (0.5 * (q2 * C_{eqcr} * f_{q2}) \\ & + (r2 * f_{q2}))_{\text{RCLKB}} + (0.5 * (s1 * C_{eqhv} * f_{s1}) + (C_{eqhf} * f_{s1}))_{\text{HCLK}}] + V_{CCI}^2 * [(p * (C_{eqo} + C_L) \\ & * f_p)_{\text{Output Buffers}}] \end{aligned}$$

where:

- m_c = Number of combinatorial cells switching at frequency f_m , typically 20% of C-cells
- m_s = Number of sequential cells switching at frequency f_m , typically 20% of R-cells
- n = Number of input buffers switching at frequency f_n , typically number of inputs / 4
- p = Number of output buffers switching at frequency f_p , typically number of outputs / 4
- $q1$ = Number of R-cells driven by routed array clock A
- $q2$ = Number of R-cells driven by routed array clock B
- $r1$ = Fixed capacitance due to routed array clock A
- $r2$ = Fixed capacitance due to routed array clock B
- $s1$ = Number of R-cells driven by dedicated array clock
- C_{eqcm} = Equivalent capacitance of combinatorial modules
- C_{eqsm} = Equivalent capacitance of sequential modules
- C_{eqi} = Equivalent capacitance of input buffers
- C_{eqcr} = Equivalent capacitance of routed array clocks
- C_{eqhv} = Variable capacitance of dedicated array clock
- C_{eqhf} = Fixed capacitance of dedicated array clock
- C_{eqo} = Equivalent capacitance of output buffers
- C_L = Average output loading capacitance, typically 10 pF
- f_{mC} = Average C-cell switching frequency, typically $F/10$
- f_{mS} = Average R-cell switching frequency, typically $F/10$
- f_n = Average input buffer switching frequency, typically $F/5$
- f_p = Average output buffer switching frequency, typically $F/5$
- f_{q1} = Frequency of routed clock A
- f_{q2} = Frequency of routed clock B
- f_{s1} = Frequency of dedicated array clock

The eX, SX-A and RTSX-S Power Calculator can be used to estimate the total power dissipation (static and dynamic) of eX devices: www.microsemi.com/soc/techdocs/calculators.aspx.

Output Buffer Delays

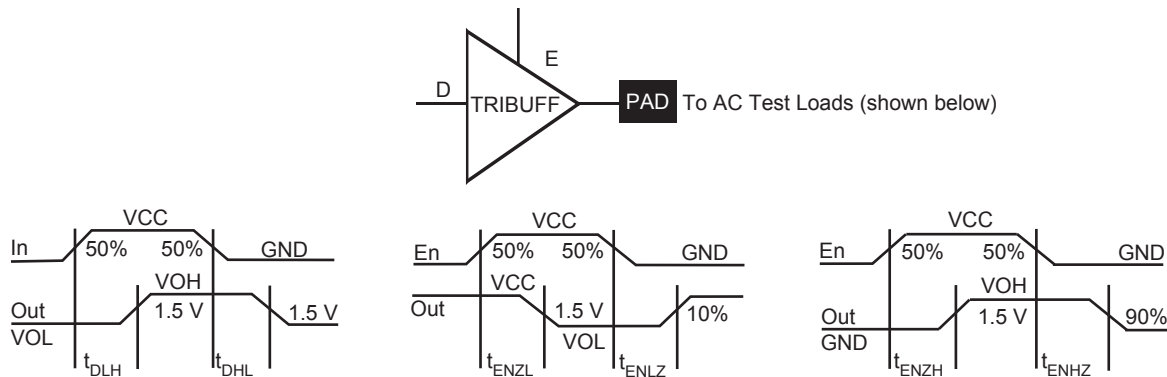


Table 1-13 • Output Buffer Delays

AC Test Loads

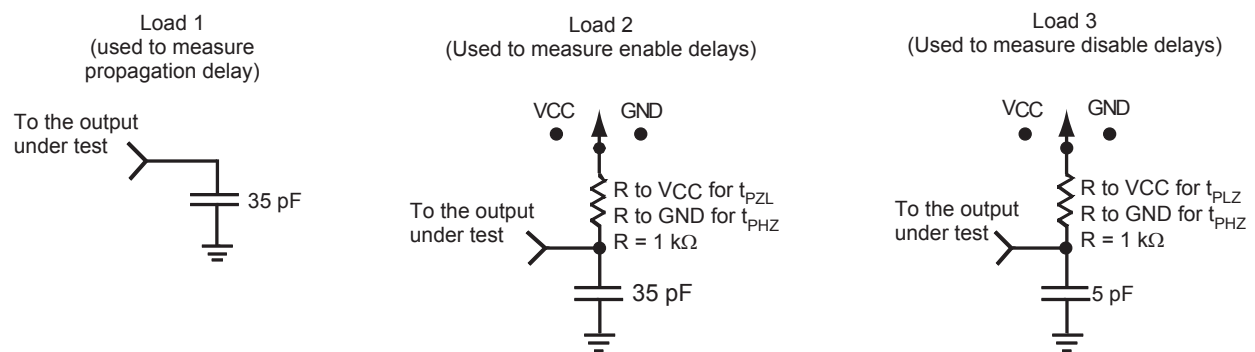


Figure 1-15 • AC Test Loads

Input Buffer Delays

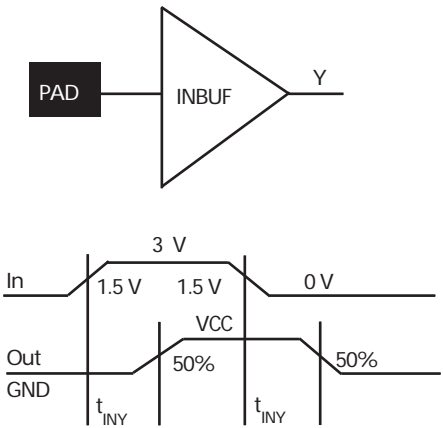


Table 1-14 • Input Buffer Delays

C-Cell Delays

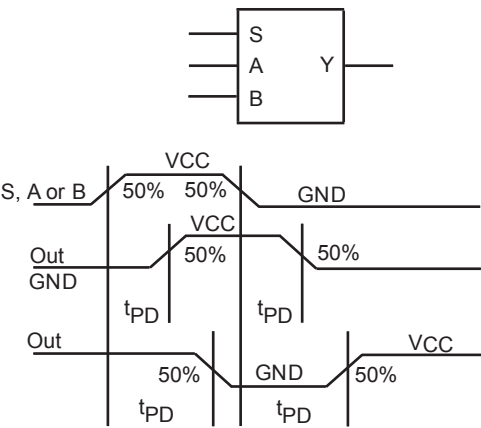


Table 1-15 • C-Cell Delays

Timing Characteristics

Timing characteristics for eX devices fall into three categories: family-dependent, device-dependent, and design-dependent. The input and output buffer characteristics are common to all eX family members. Internal routing delays are device-dependent. Design dependency means actual delays are not determined until after placement and routing of the user's design are complete. Delay values may then be determined by using the Timer utility or performing simulation with post-layout delays.

Critical Nets and Typical Nets

Propagation delays are expressed only for typical nets, which are used for initial design performance evaluation. Critical net delays can then be applied to the most timing critical paths. Critical nets are determined by net property assignment prior to placement and routing. Up to six percent of the nets in a design may be designated as critical.

Long Tracks

Some nets in the design use long tracks. Long tracks are special routing resources that span multiple rows, columns, or modules. Long tracks employ three to five antifuse connections. This increases capacitance and resistance, resulting in longer net delays for macros connected to long tracks. Typically, no more than six percent of nets in a fully utilized device require long tracks. Long tracks contribute approximately 4 ns to 8.4 ns delay. This additional delay is represented statistically in higher fanout routing delays.

Timing Derating

eX devices are manufactured with a CMOS process. Therefore, device performance varies according to temperature, voltage, and process changes. Minimum timing parameters reflect maximum operating voltage, minimum operating temperature, and best-case processing. Maximum timing parameters reflect minimum operating voltage, maximum operating temperature, and worst-case processing.

Temperature and Voltage Derating Factors

Table 1-16 • Temperature and Voltage Derating Factors
(Normalized to Worst-Case Commercial, $T_J = 70^\circ\text{C}$, $V_{CCA} = 2.3\text{V}$)

VCCA	Junction Temperature (T_J)						
	-55	-40	0	25	70	85	125
2.3	0.79	0.80	0.87	0.88	1.00	1.04	1.13
2.5	0.74	0.74	0.81	0.83	0.93	0.97	1.06
2.7	0.69	0.70	0.76	0.78	0.88	0.91	1.00

Table 1-18 • eX Family Timing Characteristics
(Worst-Case Commercial Conditions VCCA = 2.3 V, VCCI = 4.75 V, T_J = 70°C)

		–P Speed		Std Speed		–F Speed		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
Dedicated (Hard-Wired) Array Clock Networks								
t _{HCKH}	Input LOW to HIGH (Pad to R-Cell Input)		1.1		1.6		2.3	ns
t _{HCKL}	Input HIGH to LOW (Pad to R-Cell Input)		1.1		1.6		2.3	ns
t _{HPWH}	Minimum Pulse Width HIGH	1.4		2.0		2.8		ns
t _{HPWL}	Minimum Pulse Width LOW	1.4		2.0		2.8		ns
t _{HCKSW}	Maximum Skew		<0.1		<0.1		<0.1	ns
t _{HP}	Minimum Period	2.8		4.0		5.6		ns
f _{HMAX}	Maximum Frequency		357		250		178	MHz
Routed Array Clock Networks								
t _{RCKH}	Input LOW to HIGH (Light Load) (Pad to R-Cell Input) MAX.		1.1		1.6		2.2	ns
t _{RCKL}	Input HIGH to LOW (Light Load) (Pad to R-Cell Input) MAX.		1.0		1.4		2.0	ns
t _{RCKH}	Input LOW to HIGH (50% Load) (Pad to R-Cell Input) MAX.		1.2		1.7		2.4	ns
t _{RCKL}	Input HIGH to LOW (50% Load) (Pad to R-Cell Input) MAX.		1.2		1.7		2.4	ns
t _{RCKH}	Input LOW to HIGH (100% Load) (Pad to R-Cell Input) MAX.		1.3		1.9		2.6	ns
t _{RCKL}	Input HIGH to LOW (100% Load) (Pad to R-Cell Input) MAX.		1.3		1.9		2.6	ns
t _{RPWH}	Min. Pulse Width HIGH	1.5		2.1		3.0		ns
t _{RPWL}	Min. Pulse Width LOW	1.5		2.1		3.0		ns
t _{RCKSW} *	Maximum Skew (Light Load)		0.2		0.3		0.4	ns
t _{RCKSW} *	Maximum Skew (50% Load)		0.1		0.2		0.3	ns
t _{RCKSW} *	Maximum Skew (100% Load)		0.1		0.1		0.2	ns

Note: *Clock skew improves as the clock network becomes more heavily loaded.

Table 1-20 • eX Family Timing Characteristics
(Worst-Case Commercial Conditions VCCA = 2.3 V, T_J = 70°C)

		–P Speed		Std Speed		–F Speed		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
2.5 V LVCMOS Output Module Timing¹ (VCCI = 2.3 V)								
t _{DLH}	Data-to-Pad LOW to HIGH		3.3		4.7		6.6	ns
t _{DHL}	Data-to-Pad HIGH to LOW		3.5		5.0		7.0	ns
t _{DHLS}	Data-to-Pad HIGH to LOW—Low Slew		11.6		16.6		23.2	ns
t _{ENZL}	Enable-to-Pad, Z to L		2.5		3.6		5.1	ns
t _{ENZLS}	Enable-to-Pad Z to L—Low Slew		11.8		16.9		23.7	ns
t _{ENZH}	Enable-to-Pad, Z to H		3.4		4.9		6.9	ns
t _{ENLZ}	Enable-to-Pad, L to Z		2.1		3.0		4.2	ns
t _{ENHZ}	Enable-to-Pad, H to Z		2.4		5.67		7.94	ns
d _{TLH}	Delta Delay vs. Load LOW to HIGH		0.034		0.046		0.066	ns/pF
d _{THL}	Delta Delay vs. Load HIGH to LOW		0.016		0.022		0.05	ns/pF
d _{THLS}	Delta Delay vs. Load HIGH to LOW—Low Slew		0.05		0.072		0.1	ns/pF
3.3 V LVTTTL Output Module Timing¹ (VCCI = 3.0 V)								
t _{DLH}	Data-to-Pad LOW to HIGH		2.8		4.0		5.6	ns
t _{DHL}	Data-to-Pad HIGH to LOW		2.7		3.9		5.4	ns
t _{DHLS}	Data-to-Pad HIGH to LOW—Low Slew		9.7		13.9		19.5	ns
t _{ENZL}	Enable-to-Pad, Z to L		2.2		3.2		4.4	ns
t _{ENZLS}	Enable-to-Pad Z to L—Low Slew		9.7		13.9		19.6	ns
t _{ENZH}	Enable-to-Pad, Z to H		2.8		4.0		5.6	ns
t _{ENLZ}	Enable-to-Pad, L to Z		2.8		4.0		5.6	ns
t _{ENHZ}	Enable-to-Pad, H to Z		2.6		3.8		5.3	ns
d _{TLH}	Delta Delay vs. Load LOW to HIGH		0.02		0.03		0.046	ns/pF
d _{THL}	Delta Delay vs. Load HIGH to LOW		0.016		0.022		0.05	ns/pF
d _{THLS}	Delta Delay vs. Load HIGH to LOW—Low Slew		0.05		0.072		0.1	ns/pF
5.0 V TTL Output Module Timing* (VCCI = 4.75 V)								
t _{DLH}	Data-to-Pad LOW to HIGH		2.0		2.9		4.0	ns
t _{DHL}	Data-to-Pad HIGH to LOW		2.6		3.7		5.2	ns
t _{DHLS}	Data-to-Pad HIGH to LOW—Low Slew		6.8		9.7		13.6	ns
t _{ENZL}	Enable-to-Pad, Z to L		1.9		2.7		3.8	ns
t _{ENZLS}	Enable-to-Pad Z to L—Low Slew		6.8		9.8		13.7	ns
t _{ENZH}	Enable-to-Pad, Z to H		2.1		3.0		4.1	ns
t _{ENLZ}	Enable-to-Pad, L to Z		3.3		4.8		6.6	ns

Note: *Delays based on 35 pF loading.

TQ64		
Pin Number	eX64 Function	eX128 Function
1	GND	GND
2	TDI, I/O	TDI, I/O
3	I/O	I/O
4	TMS	TMS
5	GND	GND
6	VCCI	VCCI
7	I/O	I/O
8	I/O	I/O
9	NC	I/O
10	NC	I/O
11	TRST, I/O	TRST, I/O
12	I/O	I/O
13	NC	I/O
14	GND	GND
15	I/O	I/O
16	I/O	I/O
17	I/O	I/O
18	I/O	I/O
19	VCCI	VCCI
20	I/O	I/O
21	PRB, I/O	PRB, I/O
22	VCCA	VCCA
23	GND	GND
24	I/O	I/O
25	HCLK	HCLK
26	I/O	I/O
27	I/O	I/O
28	I/O	I/O
29	I/O	I/O
30	I/O	I/O
31	I/O	I/O
32	TDO, I/O	TDO, I/O

TQ64		
Pin Number	eX64 Function	eX128 Function
33	GND	GND
34	I/O	I/O
35	I/O	I/O
36	VCCA	VCCA
37	VCCI	VCCI
38	I/O	I/O
39	I/O	I/O
40	NC	I/O
41	NC	I/O
42	I/O	I/O
43	I/O	I/O
44	VCCA	VCCA
45*	GND/LP	GND/ LP
46	GND	GND
47	I/O	I/O
48	I/O	I/O
49	I/O	I/O
50	I/O	I/O
51	I/O	I/O
52	VCCI	VCCI
53	I/O	I/O
54	I/O	I/O
55	CLKA	CLKA
56	CLKB	CLKB
57	VCCA	VCCA
58	GND	GND
59	PRA, I/O	PRA, I/O
60	I/O	I/O
61	VCCI	VCCI
62	I/O	I/O
63	I/O	I/O
64	TCK, I/O	TCK, I/O

Note: *Please read the LP pin descriptions for restrictions on their use.

TQ100			
Pin Number	eX64 Function	eX128 Function	eX256 Function
71	I/O	I/O	I/O
72	NC	I/O	I/O
73	NC	NC	I/O
74	NC	NC	I/O
75	NC	NC	I/O
76	NC	I/O	I/O
77	I/O	I/O	I/O
78	I/O	I/O	I/O
79	I/O	I/O	I/O
80	I/O	I/O	I/O
81	I/O	I/O	I/O
82	VCCI	VCCI	VCCI
83	I/O	I/O	I/O
84	I/O	I/O	I/O
85	I/O	I/O	I/O
86	I/O	I/O	I/O
87	CLKA	CLKA	CLKA
88	CLKB	CLKB	CLKB
89	NC	NC	NC
90	VCCA	VCCA	VCCA
91	GND	GND	GND
92	PRA, I/O	PRA, I/O	PRA, I/O
93	I/O	I/O	I/O
94	I/O	I/O	I/O
95	I/O	I/O	I/O
96	I/O	I/O	I/O
97	I/O	I/O	I/O
98	I/O	I/O	I/O
99	I/O	I/O	I/O
100	TCK, I/O	TCK, I/O	TCK, I/O

Note: *Please read the LP pin descriptions for restrictions on their use.

Revision	Changes	Page
Advance v0.4	In the Product Profile , the Maximum User I/Os for eX64 was changed to 84.	1-I
	In the Product Profile table, the Maximum User I/Os for eX128 was changed to 100.	1-I
Advance v0.3	The Mechanical Drawings section has been removed from the data sheet. The mechanical drawings are now contained in a separate document, "Package Characteristics and Mechanical Drawings," available on the Actel web site.	
	A new section describing " Clock Resources " has been added.	1-3
	A new table describing " I/O Features " has been added.	1-6
	The " Pin Description " section has been updated and clarified.	1-31
	The original Electrical Specifications table was separated into two tables (2.5V and 3.3/5.0V). In both tables, several different currents are specified for V_{OH} and V_{OL} .	Page 8 and 9
	A new table listing 2.5V low power specifications and associated power graphs were added.	page 9
	Pin functions for eX256 TQ100 have been added to the " TQ100 " table.	2-3
	A CS49 pin drawing and pin assignment table including eX64 and eX128 pin functions have been added.	page 26
	A CS128 pin drawing and pin assignment table including eX64, eX128, and eX256 pin functions have been added.	pages 26-27
	A CS180 pin drawing and pin assignment table for eX256 pin functions have been added.	pages 27, 31
Advance v0.2	The following table note was added to the eX Timing Characteristics table for clarification: Clock skew improves as the clock network becomes more heavily loaded.	pages 14-15

